

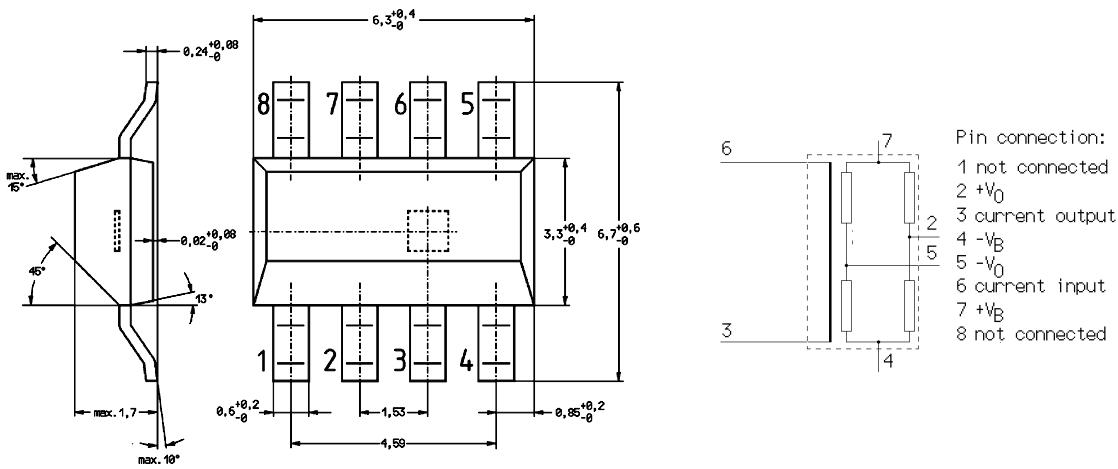
### Function principle

Magnetoresistive materials can change their resistivity in an external magnetic field. The variation of the resistivity is determined by the rotation of magnetisation with respect to the direction of the current flow. Permalloy ( $Ni_{81}Fe_{19}$ ) is commercially used as magnetoresistive material. The relative change of resistivity is 2-3 % for this material. The high sensitive and small size sensor consists of a silicon chip coated with thin film permalloy stripes. These stripes form a Wheatstone bridge, whose output voltage depends on the magnetic field.

### Characteristic

The sensor chip measures the magnetic field generated by an internal current-carrying conductor. The current sensor has an integrated permanent magnet. No external auxiliary field  $H_x$  is required. A direct or alternating current  $I_M$  up to 5 A can be detected.

### Package: mod. SM-8



## Sensors in thin film technology

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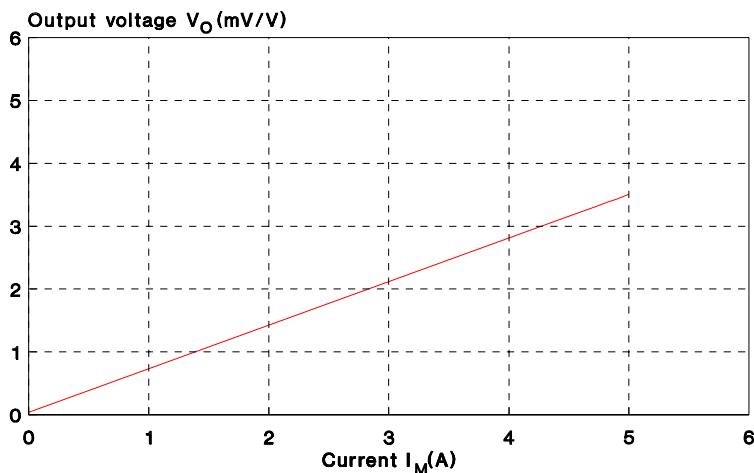
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**Technical data**

<b>Absolute maximum ratings</b>				<i>Test conditions for Input-Output Insulation:</i>	
<b>Parameter</b>	<b>Symbol</b>	<b>Unit</b>	<b>Value</b>		
Supply voltage	$V_B$	V	12		
Measurable current	$I_M$	A	5		
Operating temperature range	$T_{amb}$	°C	-40 ... +125		
Storage temperature range	$T_{stg}$	°C	-65 ... +150		

<b>Electrical characteristics ( <math>T_{amb} = 25^\circ\text{C}</math> )</b>					
<b>Parameter</b>	<b>Symbol</b>	<b>Unit</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>
Bridge resistance	$R_B$	kOhm	1.4	1.7	2.2
Offset voltage	$V_{OFF}/V_B$	mV/V	-	-	±2
Open circuit sensitivity	$S$	(mV/V)/A	-	0.7	-
Resistance of the conductor	$R$	mOhm	-	0.7	-
Operating frequency	$f_{max}$	kHz	-	-	100
Temperature coefficient of open circuit sensitivity	$T_C$	%/K	-	-	-0.3
Input-Output Insulation	$I_{I-O}$	nA	-	-	100



KMC 05 output voltage  $V_o$  versus current  $I_M$  for an auxiliary field  $H_x$  created by an internal magnet

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